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High Voltage Transistors

NPN Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
	MMBT5550 MMBT5551	V _{CEO}	140 160	Vdc
	MMBT5550 MMBT5551	V _{CBO}	160 180	Vdc
Emitter-Base Voltage		V _{EBO}	6.0	Vdc
Collector Current – Continuous		Ι _C	600	mAdc
Electrostatic Discharge Human Body Model Machine Model		ESD	> 8000 > 400	V

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T _A = 25°C Derate Above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) @T _A = 25°C Derate Above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

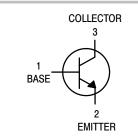
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

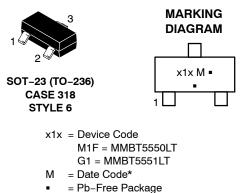
2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.



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(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT5550LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5550LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT5551LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT5551LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5551LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBT5551LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

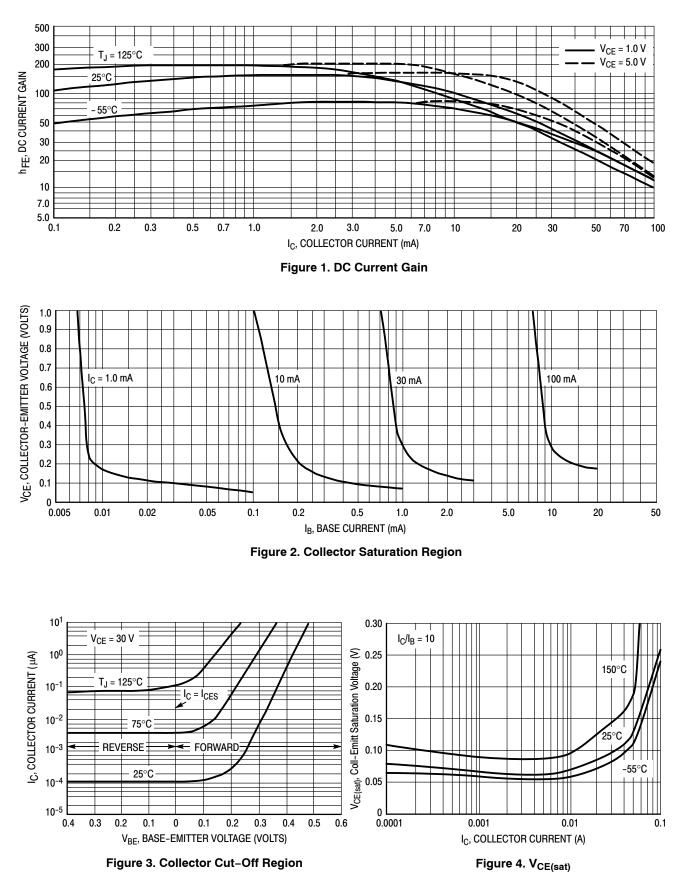
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise noted)

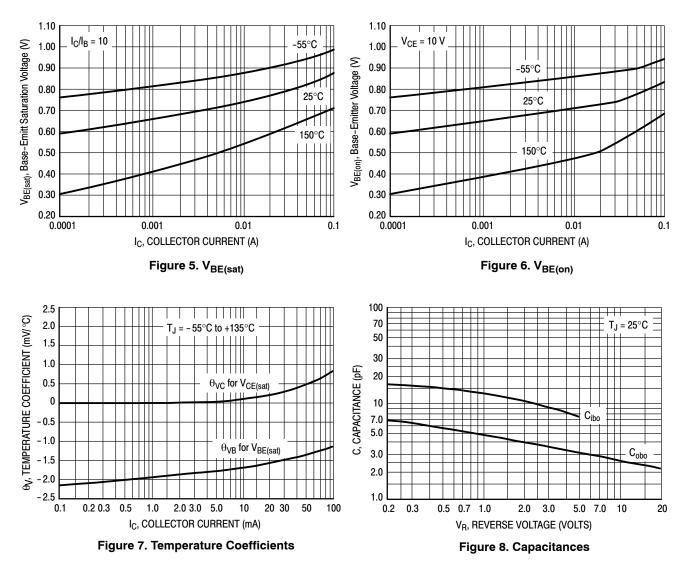
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 3) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MMBT5550 MMBT5551	V _{(BR)CEO}	140 160		Vdc
Collector – Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	MMBT5550 MMBT5551	V _{(BR)CBO}	160 180		Vdc
Emitter – Base Breakdown Voltage $(I_E = 10 \ \mu Adc, I_C = 0)$		V _{(BR)EBO}	6.0	_	Vdc
	MMBT5550 MMBT5551 MMBT5550 MMBT5551	I _{CBO}	- - - -	100 50 100 50	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 4.0 \text{ Vdc}, I_C = 0$)		I _{EBO}	_	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	MMBT5550 MMBT5551 MMBT5550 MMBT5551 MMBT5550 MMBT5551	h _{FE}	60 80 60 80 20 30	 250 250 	-
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)	Both Types MMBT5550 MMBT5551	V _{CE(sat)}	- - -	0.15 0.25 0.20	Vdc
Base – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)	Both Types MMBT5550 MMBT5551	V _{BE(sat)}	- - -	1.0 1.2 1.0	Vdc
Collector Emitter Cut-off $(V_{CB} = 10 V)$ $(V_{CB} = 75 V)$	Both Types	I _{CES}		50 100	nA

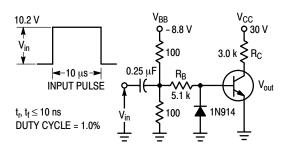
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

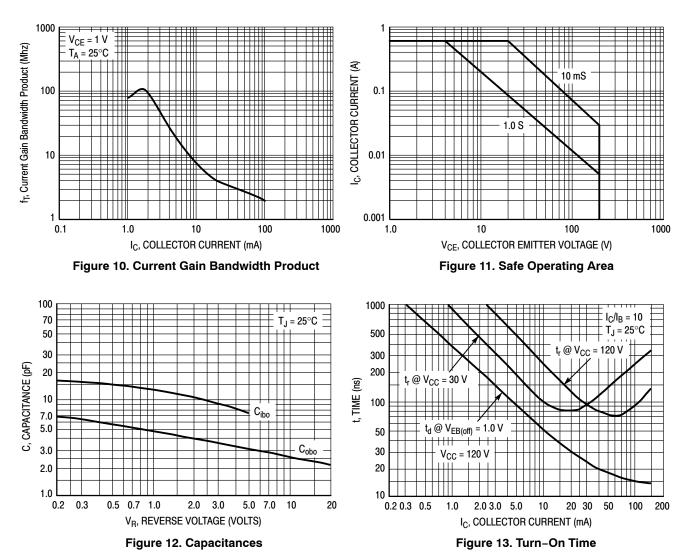




Values Shown are for $I_C \ensuremath{ @ } 10 \mbox{ mA}$

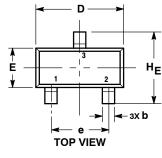
Figure 9. Switching Time Test Circuit

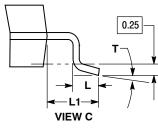
TYPICAL CHARACTERISTICS



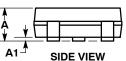
PACKAGE DIMENSIONS

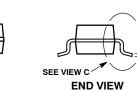
SOT-23 (TO-236) CASE 318-08 **ISSUE AR**





С





NOTES:

- DIES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE DOC MATERIA. THE BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- 4. PROTRUSIONS, OR GATE BURRS.

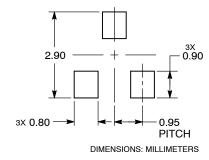
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10 °	0 °		10 °

STYLE 6: PIN 1. BASE

2. EMITTER

3 COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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